

Vishay Siliconix

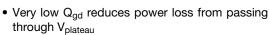
# N-Channel 80 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	80				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0032				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0034				
Q <sub>g</sub> typ. (nC)	94				
I <sub>D</sub> (A)	120 <sup>d</sup>				
Configuration	Single				

#### **FEATURES**

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature

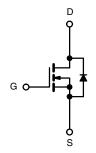




- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- Power supply
  - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and halogen-free	SUM60030E-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	80	V		
Gate-source voltage	V <sub>GS</sub>	± 20	v		
Continuous drain surrent /T 150 °C)	T <sub>C</sub> = 25 °C		120 <sup>d</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	120 <sup>d</sup>	1	
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	500	A	
Avalanche current		I <sub>AS</sub>	70	1	
Single avalanche energy <sup>a</sup> L = 0.1 mH		E <sub>AS</sub>	245	mJ	
	T <sub>C</sub> = 25 °C	Б	375 b	W	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125 <sup>b</sup>		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/M		
Junction-to-case (drain)	R <sub>thJC</sub>	0.4	°C/W		

### Notes

- a. Duty cycle  $\leq 1 \%$ .
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Package limited.



www.vishay.com

# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•			
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-		
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	μΑ	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150		
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	Α	
Duning and a state was interest of		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.0026	0.0032		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A	-	0.0028	0.0034	Ω	
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	100	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	7910	-	pF	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 40 V, f = 1 MHz	-	3250	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	348	-		
Total gate charge <sup>c</sup>	Qg		-	94	141		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	31	-	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	10	-	1	
Gate resistance	Rg	f = 1 MHz	0.28	1.4	2.8	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	24	40		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 40 \text{ V}, R_L = 4 \Omega$	-	24	40		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D\cong 10~A,~V_{GEN}=10~V,~R_g=1~\Omega$	-	34	60	ns	
Fall time <sup>c</sup>	t <sub>f</sub>		-	14	28		
Drain-Source Body Diode Ratings	and Characte	ristics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	250	Α	
Forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V	
Reverse recovery time	t <sub>rr</sub>		-	126	190	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>	$I_F = 34 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse recovery charge	Q <sub>rr</sub>		-	0.315	0.475	μC	

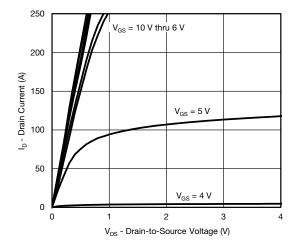
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

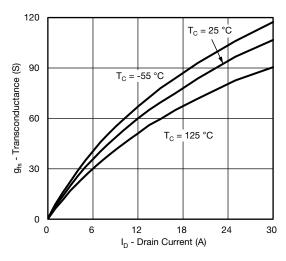
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



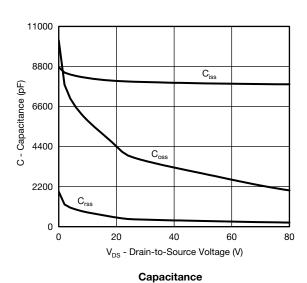
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### **Output Characteristics**



#### Transconductance

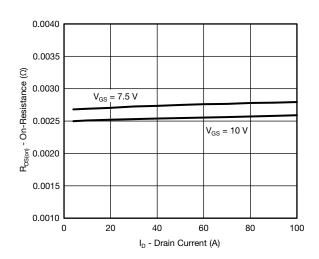


S16-2098-Rev. B, 10-Oct-16

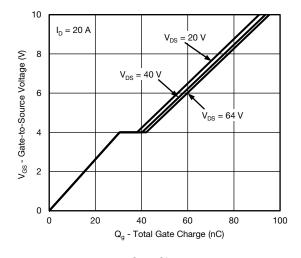
100

80

#### **Transfer Characteristics**

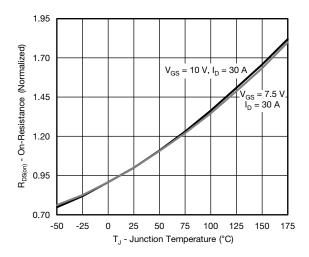


On-Resistance vs. Drain Current

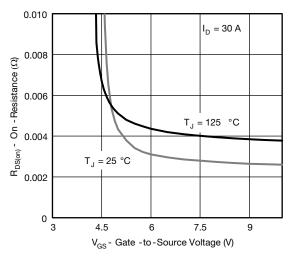




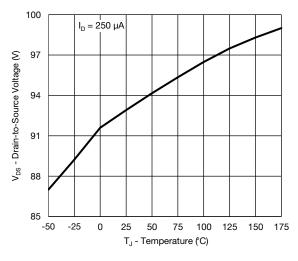
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



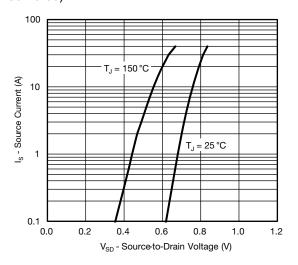
#### On-Resistance vs. Junction Temperature



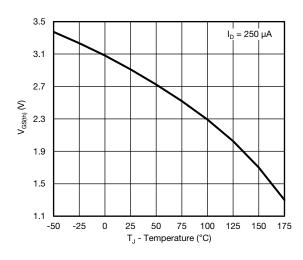
On-Resistance vs. Gate-to-Source Voltage



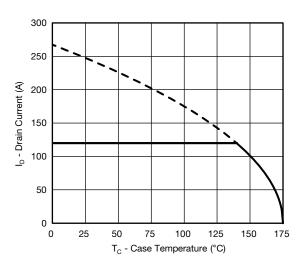
Drain Source Breakdown vs. Junction Temperature



#### **Source Drain Diode Forward Voltage**



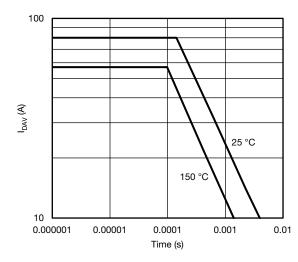
### Threshold Voltage



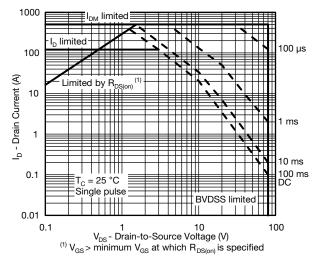
**Current De-rating** 



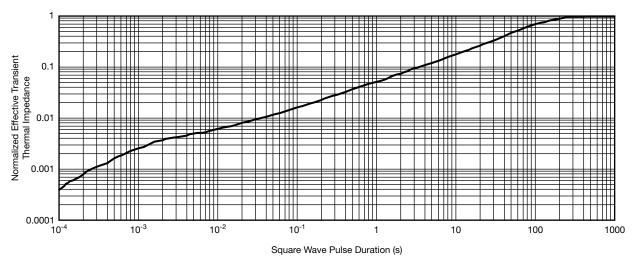
### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



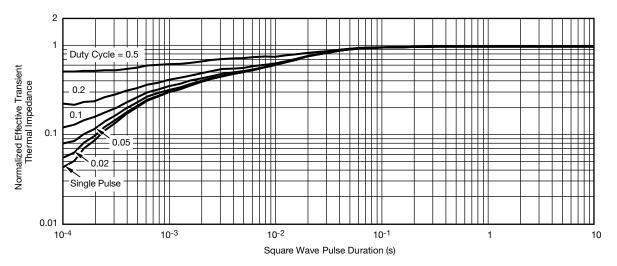
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

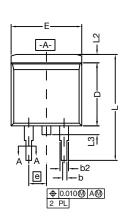
#### Note

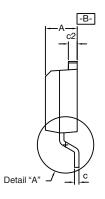
- · The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual pplication parameters and operating conditions.

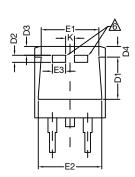
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267984">www.vishay.com/ppg267984</a>.



# TO-263 (D<sup>2</sup>PAK): 3-LEAD

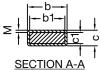








DETAIL A (ROTATED 90°)



⋝:	b     b1	ţ
2:	T /////// 5	
	SECTION A.	Ţ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

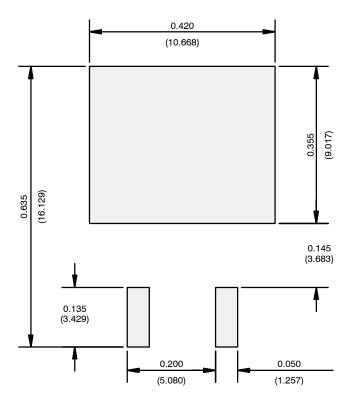
		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	) BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





### RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



## **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

SUM60030E-GE3